Accepted Manuscript

Investigating the effect of silicon thickness on ultra-thin silicon on insulator as a compliant substrate for gallium arsenide heteroepitaxial growth thin stand films

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PII: S0040-6090(18)30200-1

DOI: doi:10.1016/j.tsf.2018.03.056

Reference: TSF 36560

To appear in: Thin Solid Films

Received date: 16 August 2017 Revised date: 7 March 2018 Accepted date: 19 March 2018

Please cite this article as: Shinyoung Noh, Xiaojing Hao, Ziheng Liu, Martin A. Green, Sammy Lee, Anita Ho-Baillie, Investigating the effect of silicon thickness on ultra-thin silicon on insulator as a compliant substrate for gallium arsenide heteroepitaxial growth. The address for the corresponding author was captured as affiliation for all authors. Please check if appropriate. Tsf(2017), doi:10.1016/j.tsf.2018.03.056

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